

WHAT IS CLAIMED IS:

1. A method of manufacturing a connection substrate, comprising steps of:

forming a metal wire on a base;

5 applying an insulating material onto the metal wire to form an insulation layer;

forming another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer, through a contact hole formed in the insulation layer; and

10 separating the metal wires and the insulation layer from the base.

2. The method of manufacturing a connection substrate according to claim 1,

wherein the step of applying an insulating material onto the metal wire, and the step of forming another metal wire, thereby connecting the metal wires are repeated at least two times.

3. The method of manufacturing of a connection substrate according to claim 1,

wherein the base comprises glass.

4. A connection substrate which is manufactured by the method of claim 1.

5. A method of manufacturing a semiconductor device, comprising:
a step of forming a connection substrate on a base, comprising,
forming a metal wire on a base, applying an insulating material onto the metal wire to form an insulation layer, and forming another metal wire on the insulation layer,
25 thereby connecting the metal wires which sandwich the insulation layer through a contact hole formed in the insulation layer;

a step of mounting a semiconductor chip on the metal wire which is bared; and

a step of separating the connection substrate from the base.

6. The method of manufacturing a semiconductor device of claim 5,
wherein a plurality of the semiconductor chips are mounted on the connection substrate.

7. The method of manufacturing a semiconductor device of claim 5,

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10. A semiconductor device manufactured by the method of claim 5.

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16. A semiconductor device manufactured by the method of claim 11.